

**Notice of References Cited**

 Application/Control No.  
 09/530,588

 Applicant(s)/Patent Under  
 Reexamination  
 MATSUSE ET AL.

 Examiner  
 Tuan Quach

 Art Unit  
 2814

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
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	B	US- -				
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	E	US- -				
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	L	US- -				
	M	US- -				

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	O	JP-9-186102-A	07-1997	Japan	Hah et al.	H01L	21/28
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
 Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.